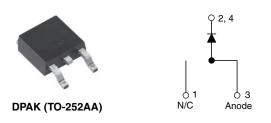
Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A



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PRIMARY CHARACTERISTICS									
I _{F(AV)}	4 A								
V _R	600 V								
V _F at I _F	1.4 V								
t _{rr} typ.	17 ns								
T _J max.	150 °C								
Package	DPAK (TO-252AA)								
Circuit configuration	Single								

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Guaranteed avalanche
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	V _{RRM}		600	V						
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4							
Single pulse forward current	I _{FSM}		25	А						
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16							
Maximum power dissipation	PD	T _C = 100 °C	10	W						
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-					
Forward voltage See fig. 1	V _F	I _F = 4 A	-	1.5	1.8	V				
		I _F = 8 A	-	1.8	2.2					
See lig. 1		I _F = 4 A, T _J = 125 °C	-	1.4	1.7					
Maximum reverse		$V_{\rm R} = V_{\rm R}$ rated	-	0.17	3.0					
leakage current	I _R	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	300	μA						
Junction capacitance	CT	V _R = 200 V	-	4	8	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

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RoHS

COMPLIANT

HALOGEN



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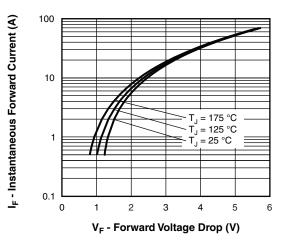
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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
Reverse recovery time		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 1.0 \text{ A}$	-	17	-					
	t _{rr}	T _J = 25 °C		-	28	42	ns			
		T _J = 125 °C	$I_F = 4 A$	-	38	57				
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.9	5.2	- A nC - A/μs			
Feak recovery current		T _J = 125 °C		-	3.7	6.7				
	Q _{rr}	T _J = 25 °C	dl _F /dt = 200 A/µs V _B = 200 V	-	40	60				
Reverse recovery charge		T _J = 125 °C	•n - 200 •	-	70	105				
Rate of fall of recovery current	dl _{(rec)M} /dt	T _J = 25 °C		-	280	-				
		T _J = 125 °C		-	235	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C				
Thermal resistance, junction to case			-	-	5.0	°C/W				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	0/10				
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style DPAK (TO-252AA)	HFA04SD60S							

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Fig. 1 - Typical Forward Voltage Drop Characteristics

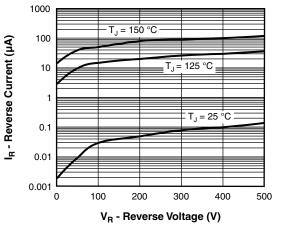


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

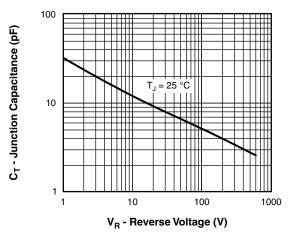
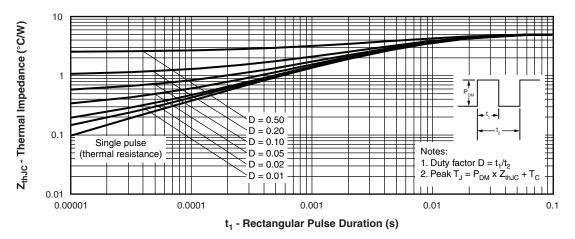


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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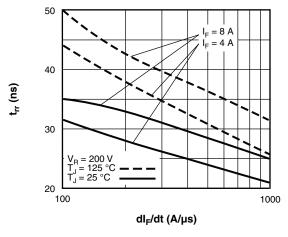


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

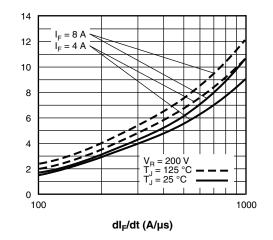


Fig. 6 - Typical Recovery Current vs. dl_F/dt

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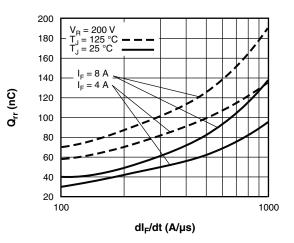


Fig. 7 - Typical Stored Charge vs. dl_F/dt

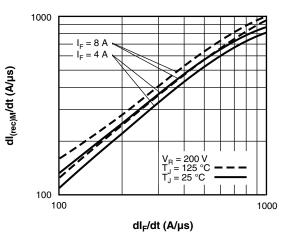


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

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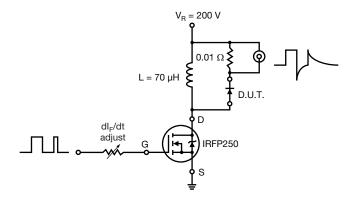


Fig. 9 - Reverse Recovery Parameter Test Circuit

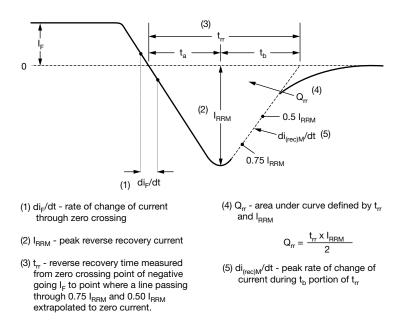


Fig. 10 - Reverse Recovery Waveform and Definitions

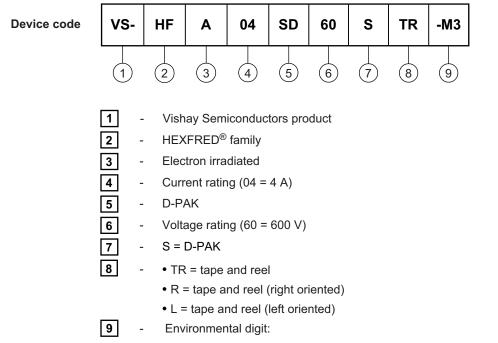
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ORDERING INFORMATION TABLE

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-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA04SD60S-M3	75	3000	Antistatic plastic tube						
VS-HFA04SD60STR-M3	2000	2000	13" diameter reel						
VS-HFA04SD60SL-M3	3000	3000	13" diameter reel						
VS-HFA04SD60SR-M3	3000	3000	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95627						
Part marking information	www.vishay.com/doc?95176						
Packaging information	www.vishay.com/doc?95033						

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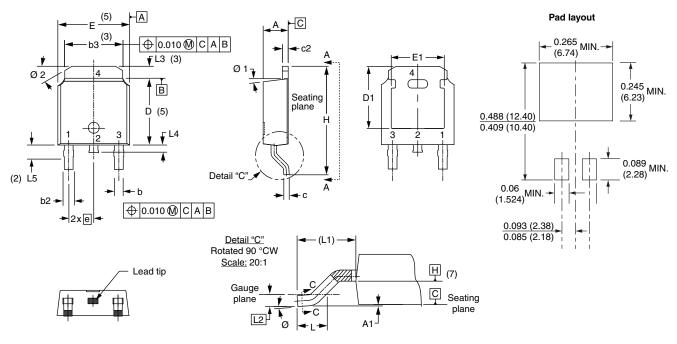


Outline Dimensions

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D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	S NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTED	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NUTES	
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC		
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410		
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070		
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.		
b3	4.95	5.46	0.195	0.215	3		L2	0.51 BSC		0.020 BSC			
С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3	
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040		
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2	
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°		
E	6.35	6.73	0.250	0.265	5]	Ø1	0°	15°	0°	15°		
E1	4.32	-	0.170	-	3]	Ø2	25°	35°	25°	35°		

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- (6) Dimension b1 and c1 applied to base metal only
- ⁽⁷⁾ Datum A and B to be determined at datum plane H
- ⁽⁸⁾ Outline conforms to JEDEC[®] outline TO-252AA



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